



TSMC-02-066

September 12, 2003

To: Commissioner for Patents  
P.O.Box 1450  
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572  
28 Davis Avenue  
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/600,393 06/20/03

Chi-Chun Chen et al.

METHOD OF FORMING DUAL GATE  
INSULATOR LAYERS FOR CMOS  
APPLICATIONS

Grp. Art Unit:

#### INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation  
In An Application.

The following Patents and/or Publications are submitted to  
comply with the duty of disclosure under CFR 1.97-1.99 and  
37 CFR 1.56. Copies of each document is included herewith.

#### CERTIFICATE OF MAILING

I hereby certify that this correspondence is being  
deposited with the United States Postal Service as first class  
mail in an envelope addressed to: Commissioner for Patents,  
P.O. Box 1450, Alexandria, VA 22313-1450, on September 19, 2003.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 9/19/03

U.S. Patent 6,110,842 to Okuno et al., "Method of Forming Multiple Gate Oxide Thicknesses Using High Density Plasma Nitridation," discloses a process for multiple gate oxides thicknesses using plasma nitridation.

U.S. Patent 6,030,862 to Kepler, "Dual Gate Oxide Formation with Minimal Channel Dopant Diffusion," discloses a DGO process.

U.S. Patent 5,960,289 to Tsui et al., "Method for Making a Dual-Thickness Gate Oxide Layer Using a Nitride/Oxide Composite Region," reveals a DGO using a N/O composition.

U.S. Patent 6,262,455 to Lutze et al., "Method of Forming Dual Gate Oxide Layers of Varying Thickness on a Single Substrate," discloses a DGO process.

U.S. Patent 6,037,224 to Buller et al., "Method for Growing Dual Oxide Thickness Using Nitrided Oxides for Oxidation Suppression," discloses a DGO using nitrided oxides.

Sincerely,

A handwritten signature in black ink, appearing to be 'SBA', written over the printed name.

Stephen B. Ackerman,  
Reg. No. 37761

Form PTO-1449

INFORMATION DISCLOSURE CITATION  
IN AN APPLICATION  
(Use several sheets if necessary)

DOIP  
SEP 22 2003  
PATENT & TRADEMARK OFFICE

Doc No. Number (Specimen)  
TSMC-02-066

Application Number  
10/600,393

Applicant  
Chi-Chun Chen et al.

Filing Date  
06/20/03

Group Art Unit

PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILED DATE & APPROPRIATE
	6110842	8/29/00	Okuno et al.	438	776	4/22/98
	6030862	2/29/00	Kepler	438	217	10/13/98
	5960289	9/28/99	Tsui et al.	438	275	6/22/98
	6262455	7/17/01	Lutze et al.	257	369	11/2/99
	6037224	3/14/00	Buller et al.	438	258	5/2/97

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)


EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant